SCHOTTKY BARRIER DIODE

Features

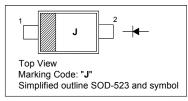
- Very low forward voltage
- Very low reverse current
- Ultra small SMD package

Applications

- Ultra high-speed switching
- Voltage clamping
- Protection circuits
- · Low power consumption applications

PINNING

PIN	DESCRIPTION
1	Cathode
2	Anode



Absolute Maximum Ratings (T_a = 25 °C)

Parameter	Symbol	Value	Unit
Reverse Voltage	V_R	40	V
Continuous Forward Current	I _F	200	mA
Repetitive Peak Forward Current t _p ≤ 1 s	I _{FRM}	300	mA
Non-repetitive Peak Forward Current (t = 8.3 ms half sinewave)	I _{FSM}	1	А
Junction Temperature	TJ	150	°C
Storage Temperature	T _s	- 65 to + 150	°C
Operating Ambient Temperature	T _{amb}	- 65 to + 150	°C

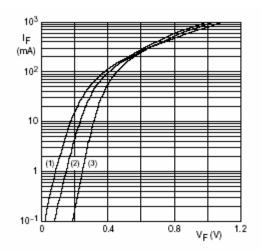
Characteristics at T_a = 25 °C

Parameter	Symbol	Max.	Unit
Forward Voltage at I_F = 0.1 mA at I_F = 1 mA at I_F = 10 mA at I_F = 100 mA at I_F = 200 mA	V _F	220 290 360 500 600	mV
Reverse Current at $V_R = 25 \text{ V}$	I _R	0.5	μΑ
Diode Capacitance at V _R = 1 V, f = 1 MHz	C _D	20	pF





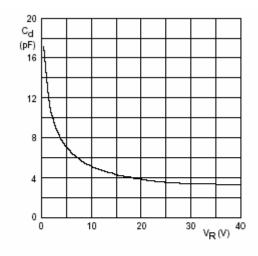






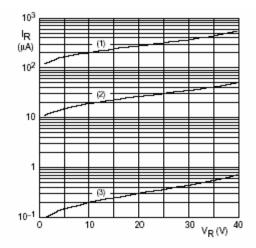
⁽²⁾ T_{amb} = 85 °C.

Fig.1 Forward current as a function of forward voltage; typical values.



f = 1 MHz; $T_{amb} = 25 \,^{\circ}\text{C}$.

Fig. 3 Diode capacitance as a function of reverse voltage; typical values.



- (1) T_{amb} = 125 °C.
- (2) T_{amb} = 85 °C.
- (3) T_{amb} = 25 °C.

Fig. 2 Reverse current as a function of reverse voltage; typical values.







⁽³⁾ T_{amb} = 25 °C.

PACKAGE OUTLINE

Plastic surface mounted package; 2 leads

SOD-523

